

P-Channel Enhancement Mode Field Effect Transistor

General Description

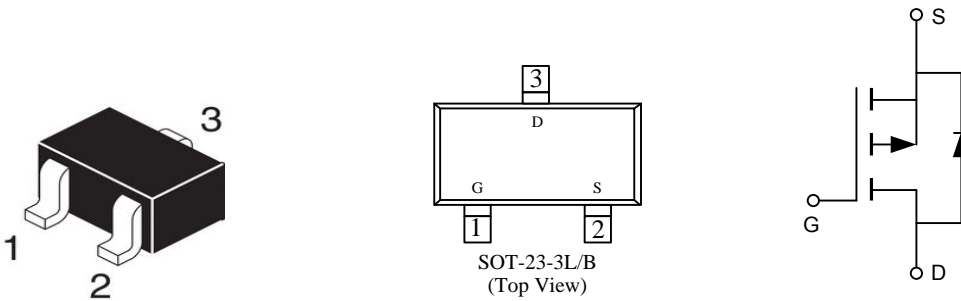
Product Summary		
V_{DSS}	I_D	$R_{DS(ON)}(m\Omega)TYP$
-20V	-0.45A	300 @ $V_{GS}=-4.5V$
	-0.35A	450 @ $V_{GS}=-2.5V$

Features

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

Package

- SOT-23-3L/B



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2307	-55°C to +150°C	SOT-23-3L/B	3000

Absolute Maximum Ratings

($T_A=25^\circ C$ unless otherwise noted)

parameter	symbol	limit	unit	
Drain-source voltage	V_{DSS}	-20	V	
Gate-source voltage	V_{GSS}	± 12	V	
Coutinuous drain current ($T_j=150^\circ C$)	I_D	$T_A=25^\circ C$	-0.8	A
		$T_A=80^\circ C$	-0.7	A
Pulsed drain current	I_{DM}	-2.8	A	
Drain-source Diode forward current	I_S	-0.58	A	
Power dissipation	P_D	$T_A=25^\circ C$	0.27	W
		$T_A=70^\circ C$	0.16	W
Operating junction Temperature range	T_j	-55—150	$^\circ C$	